



DRV5053 模拟双极霍尔效应传感器

1 特性

- 线性输出霍尔传感器
- 出色的温度稳定性
 - 温度范围内的灵敏度为 $\pm 10\%$
- 高灵敏度选项：
 - -11mV/mT (OA, 请见图 17)
 - -23mV/mT (PA)
 - -45mV/mT (RA)
 - -90mV/mT (VA)
 - $+23\text{mV/mT}$ (CA)
 - $+45\text{mV/mT}$ (EA)
- 支持宽电压范围
 - 2.5V 至 38V
 - 无需外部稳压器
- 宽运行电压范围
 - $T_A = -40^\circ\text{C}$ 至 125°C (Q, 请见图 17)
- 放大的输出级
 - 2.3mA 灌电流, 300 μA 拉电流
- 输出电压: 0.2V 至 1.8V
 - $B = 0\text{mT}$, $\text{OUT} = 1\text{V}$
- 快速上电: 35 μs
- 小型封装尺寸
 - 表面贴装 3 引脚小外形尺寸晶体管 (SOT)-23 (DBZ)
 - $2.92\text{mm} \times 2.37\text{mm}$
 - 插入式 3 引脚系统级封装 (SIP) (LPG)
 - $4.00\text{mm} \times 3.15\text{mm}$
- 保护特性
 - 反向电源保护 (高达 -22V)
 - 支持高达 40V 抛负载
 - 输出短路保护
 - 输出电流限制

2 应用

- 流量计
- 对接调整
- 振动校正
- 减震器控制

3 说明

DRV5053 器件是一款斩波稳定霍尔 IC, 能够在整个温度范围内提供具有出色灵敏度稳定性和集成保护特性的磁场感测解决方案。

0V 至 2V 模拟输出可对施加的磁感应强度做出线性响应, 并且能够辨别磁场方向的极性。反向极性保护高达 -22V 的宽工作电压范围 (2.5V 至 38V) 使得此器件适用于广泛的工业和消费类应用。

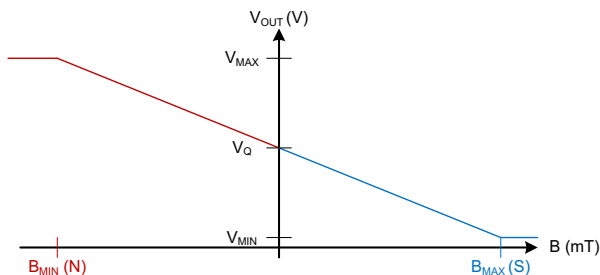
针对反向电源情况、负载突降和输出短路或过流提供内部保护功能。

器件信息⁽¹⁾

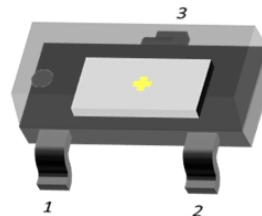
器件型号	封装	封装尺寸 (标称值)
DRV5053	SOT-23 (3)	$2.92\text{mm} \times 2.37\text{mm}$
	SIP (3)	$4.00\text{mm} \times 3.15\text{mm}$

(1) 要了解所有可用封装, 请见数据表末尾的可订购产品附录。

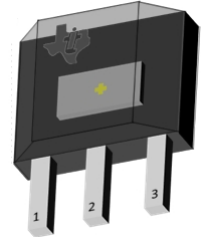
4 输出状态



SOT-23



SIP



目录

1	特性	1	8	Detailed Description	8
2	应用	1	8.1	Overview	8
3	说明	1	8.2	Functional Block Diagram	8
4	输出状态	1	8.3	Feature Description	9
5	修订历史记录	2	8.4	Device Functional Modes	11
6	Pin Configuration and Functions	3	9	Application and Implementation	12
7	Specifications	4	9.1	Application Information	12
7.1	Absolute Maximum Ratings	4	9.2	Typical Applications	12
7.2	ESD Ratings	4	10	Power Supply Recommendations	14
7.3	Recommended Operating Conditions	4	11	器件和文档支持	15
7.4	Thermal Information	4	11.1	器件支持	15
7.5	Electrical Characteristics	5	11.2	商标	16
7.6	Switching Characteristics	5	11.3	静电放电警告	16
7.7	Magnetic Characteristics	5	11.4	术语表	16
7.8	Typical Characteristics	7	12	机械封装和可订购信息	16

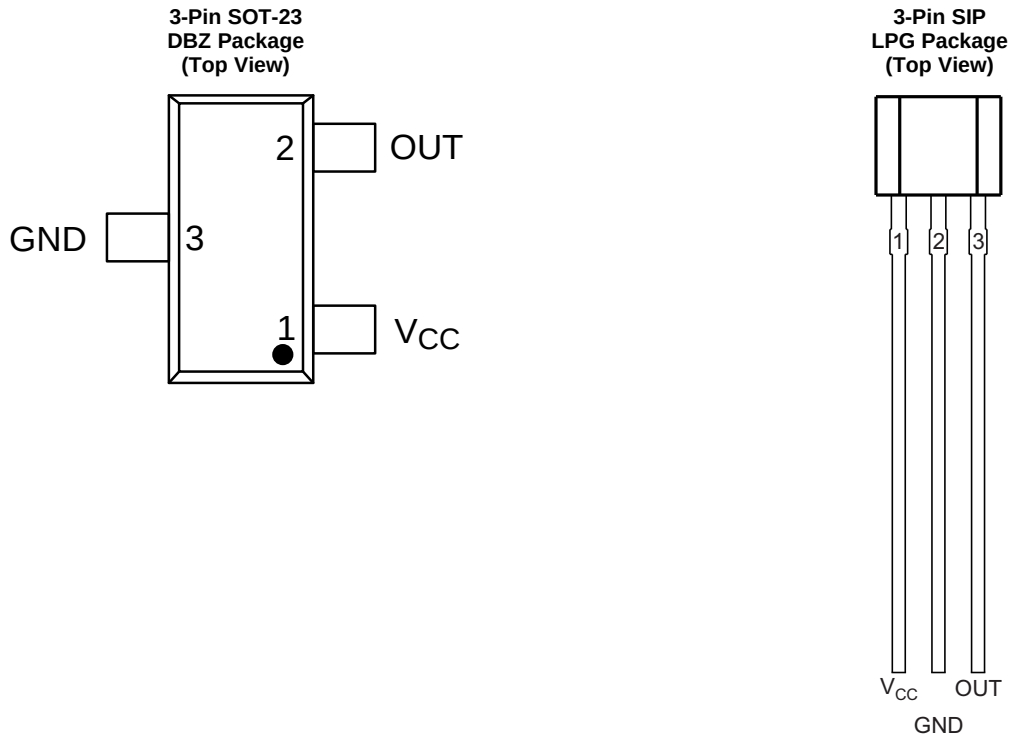
5 修订历史记录

Changes from Revision A (August 2014) to Revision B	Page
• 已更新高灵敏度选项	1
• Updated the sensitivity device values and typicals. Updated typical and max values for DRV5053VA: –80 mV/mT	6
• Updated <i>Typical Characteristics</i> graphs	7

Changes from Original (May 2014) to Revision A	Page
• 器件状态更新为量产数据	1
• Changed the maximum T _J value from 175°C to 150°C	4
• Updated <i>Magnetic Characteristics</i> table.	5

6 Pin Configuration and Functions

For additional configuration information, see [器件标记](#) and [机械封装和可订购信息](#).



Pin Functions

PIN			TYPE	DESCRIPTION
NAME	DBZ	LPG		
GND	3	2	GND	Ground pin
V _{CC}	1	1	Power	2.5 to 38 V power supply. Bypass this pin to the GND pin with a 0.01-μF (minimum) ceramic capacitor rated for V _{CC} .
OUT	2	3	Output	Hall sensor analog output. 1 V output corresponds to B = 0 mT

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
Power supply voltage	V _{CC}	–22 ⁽²⁾	40	V
	Voltage ramp rate (V _{CC}), V _{CC} < 5 V	Unlimited		V/μs
	Voltage ramp rate (V _{CC}), V _{CC} > 5 V	0	2	
Output pin voltage	OUT	–0.5	2.5	V
Output pin reverse current during reverse supply condition	OUT	0	–20	mA
Operating junction temperature	T _J	–40	150 ⁽³⁾	°C
T _{stg}	Storage temperature range	–65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) Ensured by design. Only tested to –20 V.
- (3) Tested in production to T_A = 125°C.

7.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	±2500
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	±500

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V _{CC}	Power supply voltage	2.5	38	V
V _{OUT}	Output pin voltage (OUT)	0	2	V
I _{SOURCE}	Output pin current source (OUT)	0	300	μA
I _{SINK}	Output pin current sink (OUT)	0	2.3	mA
T _A	Operating ambient temperature	–40	125	°C

7.4 Thermal Information

THERMAL METRIC ⁽¹⁾		DRV5053		UNIT
		DBZ	LPG	
		3 PINS	3 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	333.2	180	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	99.9	98.6	
R _{θJB}	Junction-to-board thermal resistance	66.9	154.9	
ψ _{JT}	Junction-to-top characterization parameter	4.9	40	
ψ _{JB}	Junction-to-board characterization parameter	65.2	154.9	

- (1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

7.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
POWER SUPPLIES (V_{CC})						
V _{CC}	V _{CC} operating voltage		2.5		38	V
I _{CC}	Operating supply current	V _{CC} = 2.5 to 38 V, T _A = 25°C		2.7		mA
		V _{CC} = 2.5 to 38 V, T _A = 125°C		3	3.6	
t _{on}	Power-on time			35	50	μs
PROTECTION CIRCUITS						
V _{CCR}	Reverse supply voltage		–22			V
I _{OCPSOURCE}	Overcurrent protection level	Sourcing current		300		μA
I _{OCPSINK}	Overcurrent protection level	Sinking current		2.3		mA

7.6 Switching Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ANALOG OUTPUT (OUT)						
t _d	Output delay time	T _A = 25°C		13	25	μs

7.7 Magnetic Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT ⁽¹⁾
V _Q	Quiescent output	B = 0 mT T _A = –40°C to 125°C	0.9	1.02	1.15	V
f _{BW}	Bandwidth ⁽²⁾		20			kHz
B _N	Input-referred noise ⁽³⁾	C _{OUT} = 50 pF T _A = –40°C to 125°C	0.40	0.58	0.79	mT _{pp}
Le	Linearity ⁽⁴⁾	–B _{SAT} < B < B _{SAT}		1%		
V _{OUT MIN}	Output saturation voltage (min)	B < –B _{SAT}			0.2	V
V _{OUT MAX}	Output saturation voltage (max)	B > B _{SAT}	1.8			V
DRV5053OA: –11 mV/mT						
S	Sensitivity	V _{CC} = 3.3 V T _A ≈ –40°C to 125°C	–17.5	–11	–5	mV/mT
V _N	Output-referred noise ⁽³⁾	V _{CC} = 3.3 V; R _{OUT} = 10 kΩ; C _{OUT} = 50 pF T _A ≈ –40°C to 125°C		6		mV _{pp}
B _{SAT}	Input saturation field	V _{CC} = 3.3 V T _A ≈ –40°C to 125°C		73		mT
DRV5053PA: –23 mV/mT						
S	Sensitivity	V _{CC} = 3.3 V T _A ≈ –40°C to 125°C	–35	–23	–10	mV/mT
V _N	Output-referred noise ⁽³⁾	V _{CC} = 3.3 V; R _{OUT} = 10 kΩ; C _{OUT} = 50 pF T _A ≈ –40°C to 125°C		13		mV _{pp}
B _{SAT}	Input saturation field	V _{CC} = 3.3 V T _A ≈ –40°C to 125°C		35		mT

(1) 1 mT = 10 Gauss

(2) Bandwidth describes the fastest changing magnetic field that can be detected and translated to the output.

(3) Not tested in production; limits are based on characterization data.

(4) Linearity describes the change in sensitivity across the B-range. The sensitivity near B_{SAT} is typically within 1% of the sensitivity near B = 0.

DRV5053

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Magnetic Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT ⁽¹⁾
DRV5053RA: –45 mV/mT						
S	Sensitivity	$V_{CC} = 3.3\text{ V}$ $T_A \approx -40^\circ\text{C to } 125^\circ\text{C}$	–70	–45	–20	mV/mT
V_N	Output-referred noise ⁽³⁾	$V_{CC} = 3.3\text{ V}$; $R_{OUT} = 10\text{ k}\Omega$; $C_{OUT} = 50\text{ pF}$ $T_A \approx -40^\circ\text{C to } 125^\circ\text{C}$		26		mV _{pp}
B_{SAT}	Input saturation field	$V_{CC} = 3.3\text{ V}$ $T_A \approx -40^\circ\text{C to } 125^\circ\text{C}$		18		mT
DRV5053VA: –90 mV/mT						
S	Sensitivity	$V_{CC} = 3.3\text{ V}$ $T_A \approx -40^\circ\text{C to } 125^\circ\text{C}$	–140	–90	–45	mV/mT
V_N	Output-referred noise ⁽³⁾	$V_{CC} = 3.3\text{ V}$; $R_{OUT} = 10\text{ k}\Omega$; $C_{OUT} = 50\text{ pF}$ $T_A \approx -40^\circ\text{C to } 125^\circ\text{C}$		52		mV _{pp}
B_{SAT}	Input saturation field	$V_{CC} = 3.3\text{ V}$ $T_A \approx -40^\circ\text{C to } 125^\circ\text{C}$		9		mT
DRV5053CA: 23 mV/mT						
S	Sensitivity	$V_{CC} = 3.3\text{ V}$ $T_A \approx -40^\circ\text{C to } 125^\circ\text{C}$	10	23	35	mV/mT
V_N	Output-referred noise ⁽³⁾	$V_{CC} = 3.3\text{ V}$; $R_{OUT} = 10\text{ k}\Omega$; $C_{OUT} = 50\text{ pF}$ $T_A \approx -40^\circ\text{C to } 125^\circ\text{C}$		13		mV _{pp}
B_{SAT}	Input saturation field	$V_{CC} = 3.3\text{ V}$ $T_A \approx -40^\circ\text{C to } 125^\circ\text{C}$		35		mT
DRV5053EA: 45 mV/mT						
S	Sensitivity	$V_{CC} = 3.3\text{ V}$ $T_A \approx -40^\circ\text{C to } 125^\circ\text{C}$	20	45	70	mV/mT
V_N	Output-referred noise ⁽³⁾	$V_{CC} = 3.3\text{ V}$; $R_{OUT} = 10\text{ k}\Omega$; $C_{OUT} = 50\text{ pF}$ $T_A \approx -40^\circ\text{C to } 125^\circ\text{C}$		26		mV _{pp}
B_{SAT}	Input saturation field	$V_{CC} = 3.3\text{ V}$ $T_A \approx -40^\circ\text{C to } 125^\circ\text{C}$		18		mT

7.8 Typical Characteristics

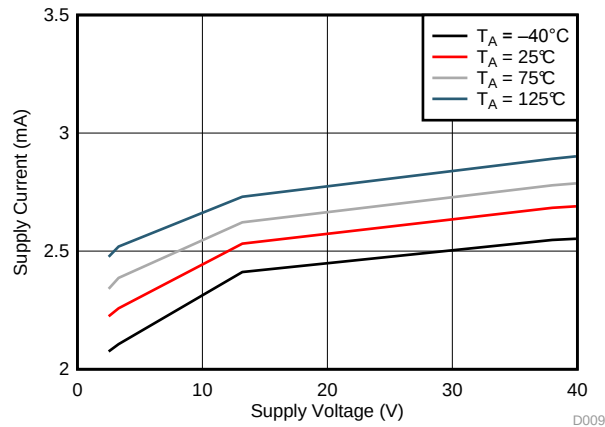


Figure 1. I_{CC} vs V_{CC}

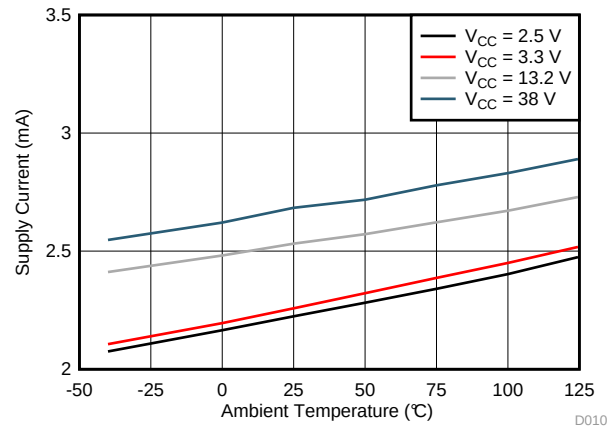


Figure 2. I_{CC} vs Temperature

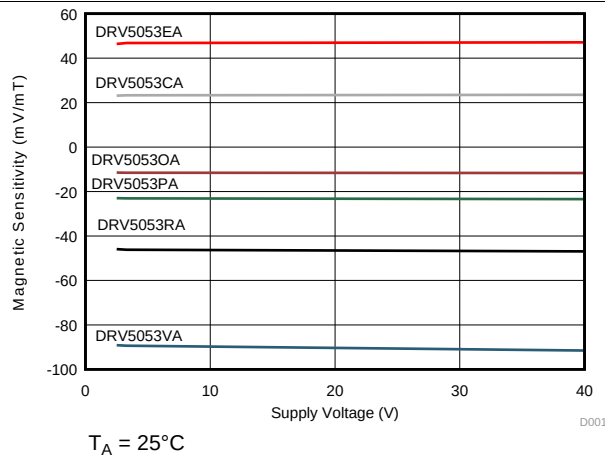


Figure 3. Sensitivity vs V_{CC}

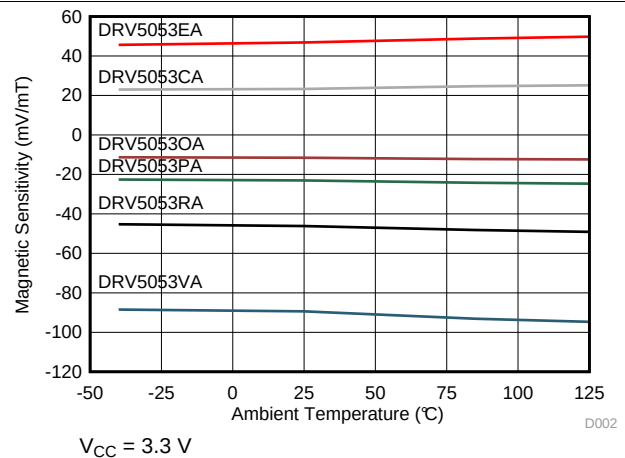


Figure 4. Sensitivity vs Temperature

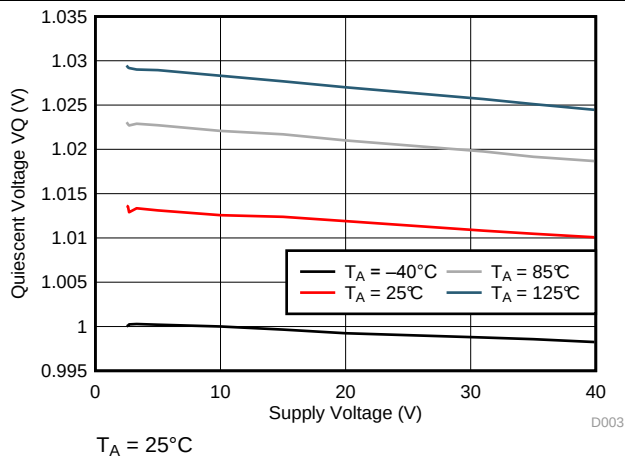


Figure 5. DRV5053AD, V_Q vs V_{CC}

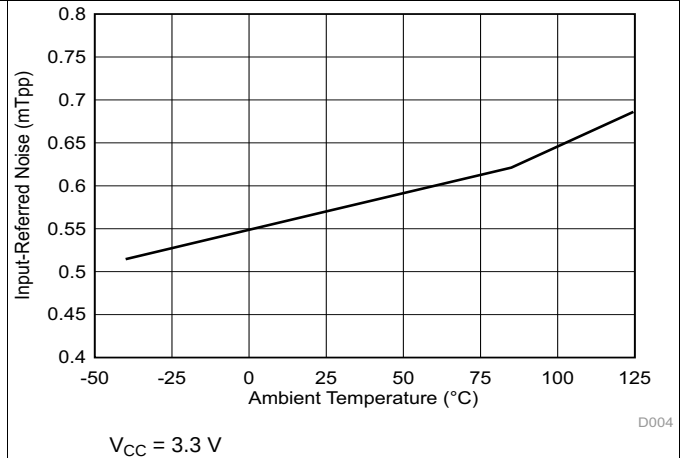


Figure 6. DRV5053AD, B_N vs Temperature

8 Detailed Description

8.1 Overview

The DRV5053 device is a chopper-stabilized hall sensor with an analog output for magnetic sensing applications. The DRV5053 device can be powered with a supply voltage between 2.5 and 38 V, and will survive -22 V reverse battery conditions continuously. Note that the DRV5053 device will not be operating when approximately -22 to 2.4 V is applied to V_{CC} (with respect to GND). In addition, the device can withstand supply voltages up to 40 V for transient durations.

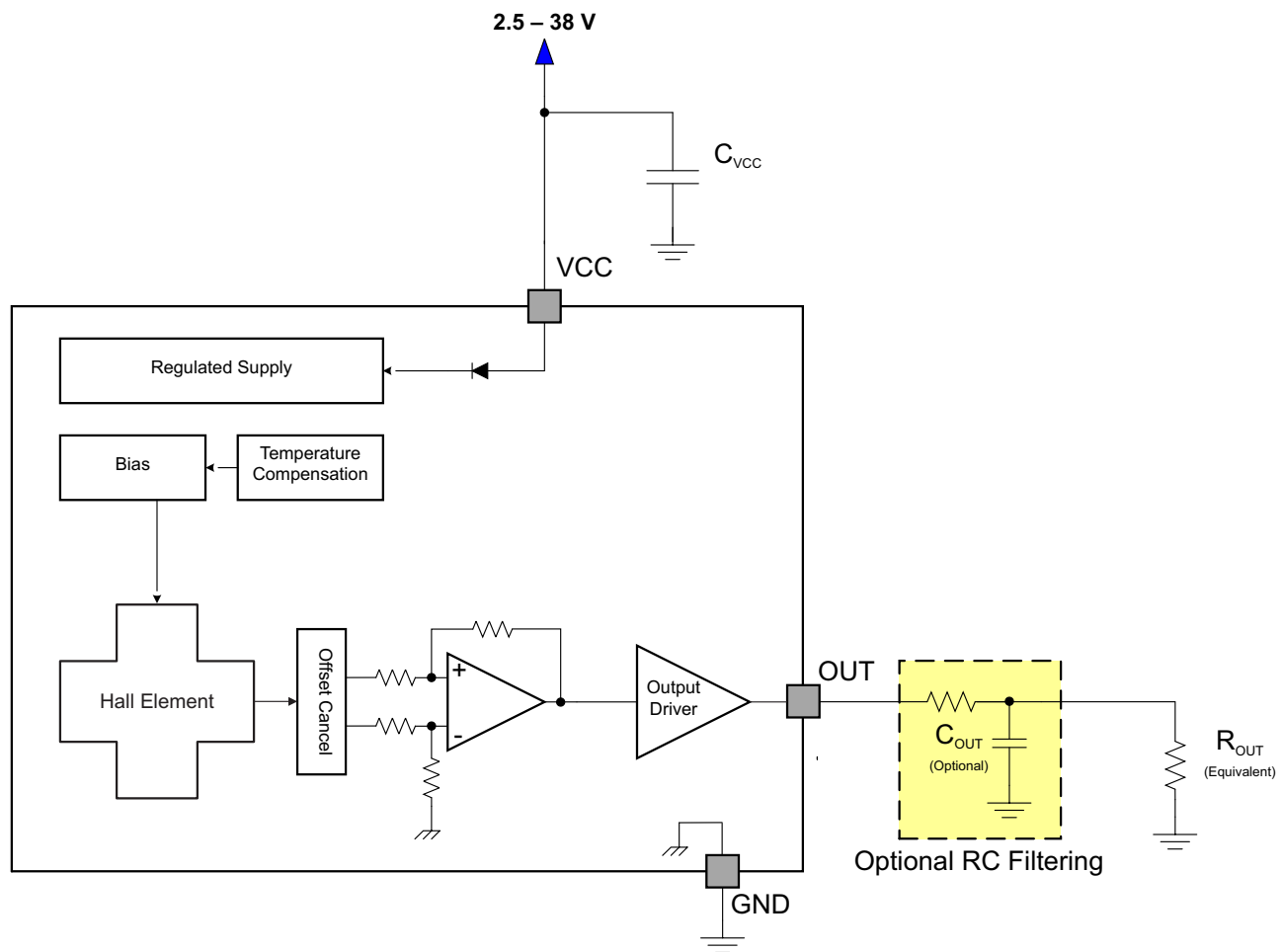
The output voltage is dependent on the magnetic field perpendicular to the package. The absence of a magnetic field will result in $OUT = 1$ V. A magnetic field will cause the output voltage to change linearly with the magnetic field.

The field polarity is defined as follows: a **south pole** near the marked side of the package is a positive magnetic field. A **north pole** near the marked side of the package is a negative magnetic field.

For devices with a negative sensitivity (that is, DRV5053RA: -40 mV/mT), a **south pole** will cause the output voltage to drop below 1 V, and a north pole will cause the output to rise above 1 V.

For devices with a positive sensitivity (that is, DRV5053EA: $+40$ mV/mT), a **south pole** will cause the output voltage to rise above 1 V, and a north pole will cause the output to drop below 1 V.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Field Direction Definition

A positive magnetic field is defined as a **south pole** near the marked side of the package as shown in [Figure 7](#).

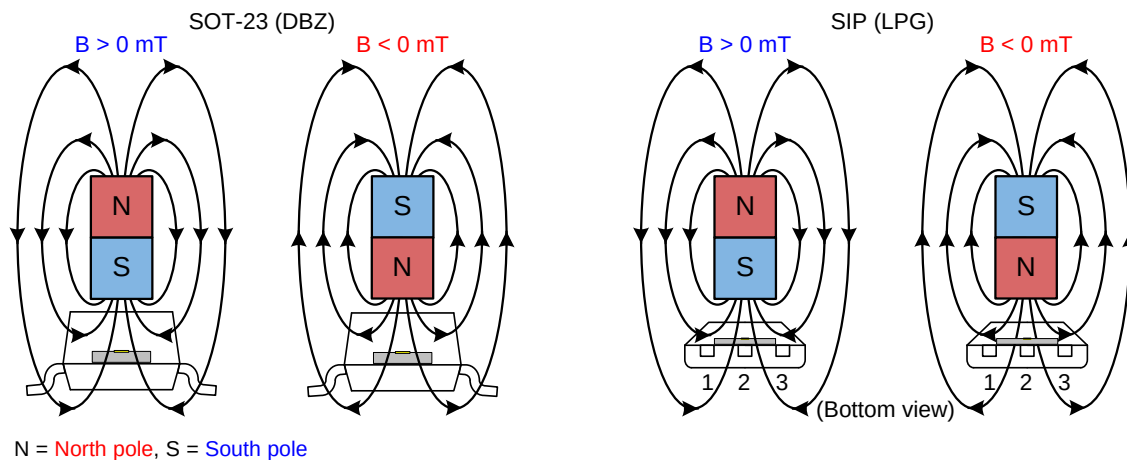


Figure 7. Field Direction Definition

8.3.2 Device Output

The DRV5053 device output is defined below for negative sensitivity (that is, -45 mV/mT , RA) and positive sensitivity (that is, $+45 \text{ mV/mT}$, EA):

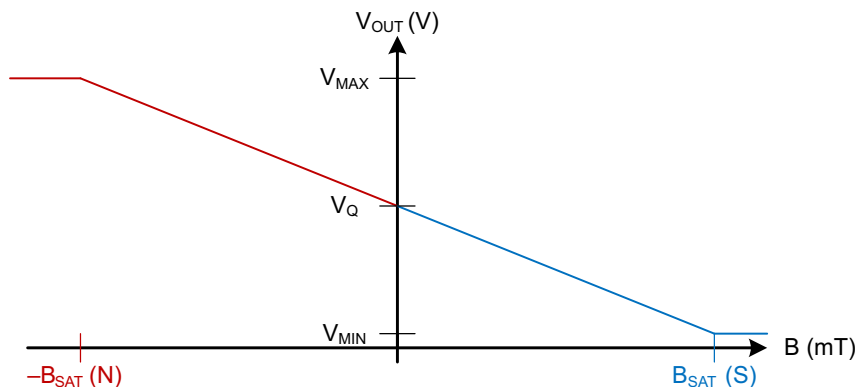


Figure 8. DRV5053 – Negative Sensitivity

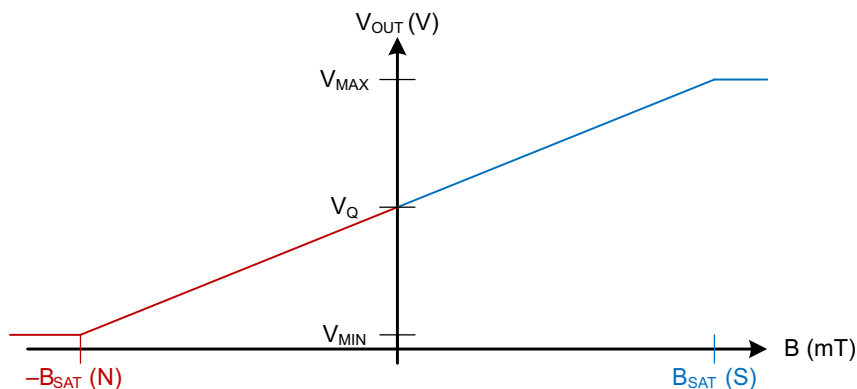


Figure 9. DRV5053 – Positive Sensitivity

Feature Description (continued)

8.3.3 Power-On Time

After applying V_{CC} to the DRV5053 device, t_{on} must elapse before OUT is valid. Figure 10 shows Case 1 and Figure 11 shows case 2; the output is defined assuming a negative sensitivity device and a constant magnetic field $-B_{SAT} < B < B_{SAT}$.

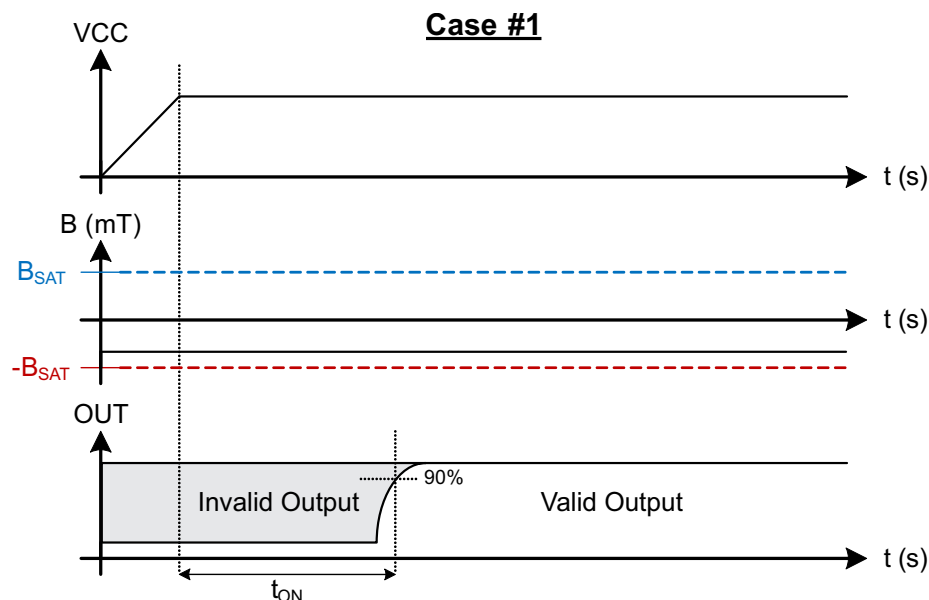


Figure 10. Case 1: Power On When $B < 0$, North

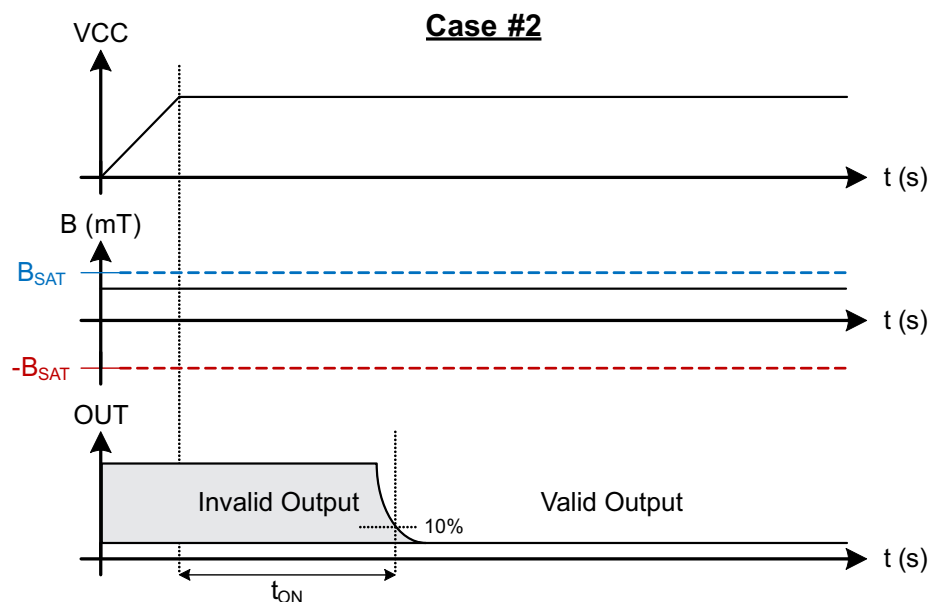


Figure 11. Case 2: Power On When $B > 0$, South

Feature Description (continued)

8.3.4 Output Stage

The DRV5053 output stage is capable of up to 300 μ A of current source or 2.3 mA sink.

For proper operation, ensure that equivalent output load $R_{OUT} > 10\text{ k}\Omega$. In addition, ensure that the load capacitance $C_{OUT} < 10\text{ nF}$.

8.3.5 Protection Circuits

An analog current limit circuit limits the current through the output driver. The driver current will be clamped to I_{OCP} .

8.3.5.1 Overcurrent Protection (OCP)

An analog current-limit circuit limits the current through the FET. The driver current is clamped to I_{OCP} . During this clamping, the $r_{DS(on)}$ of the output FET is increased from the nominal value.

8.3.5.2 Load Dump Protection

The DRV5053 device operates at DC V_{CC} conditions up to 38 V nominally, and can additionally withstand $V_{CC} = 40\text{ V}$. No current-limiting series resistor is required for this protection.

8.3.5.3 Reverse Supply Protection

The DRV5053 device is protected in the event that the V_{CC} pin and the GND pin are reversed (up to -22 V).

NOTE

In a reverse supply condition, the OUT pin reverse-current must not exceed the ratings specified in the [Absolute Maximum Ratings](#).

Table 1.

FAULT	CONDITION	DEVICE	DESCRIPTION	RECOVERY
FET overload (OCP)	$I_{SINK} \geq I_{OCP}$	Operating	Output current is clamped to I_{OCP}	$I_O < I_{OCP}$
Load Dump	$38\text{ V} < V_{CC} < 40\text{ V}$	Operating	Device will operate for a transient duration	$V_{CC} \leq 38\text{ V}$
Reverse Supply	$-22\text{ V} < V_{CC} < 0\text{ V}$	Disabled	Device will survive this condition	$V_{CC} \geq 2.5\text{ V}$

8.4 Device Functional Modes

The DRV5053 device is active only when V_{CC} is between 2.5 and 38 V.

When a reverse supply condition exists, the device is inactive.

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The DRV5053 device is used in magnetic-field sensing applications.

9.2 Typical Applications

9.2.1 Typical Application With No Filter

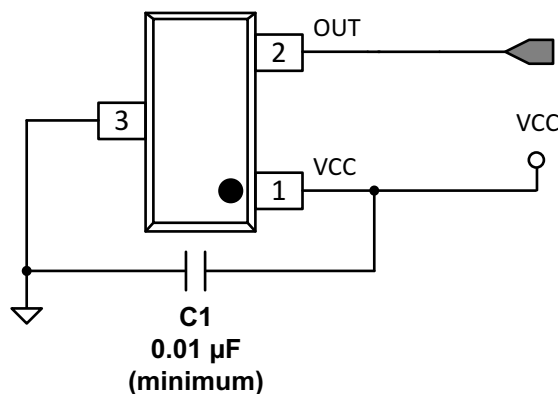


Figure 12. Typical Application Schematic – No Filter

9.2.1.1 Design Requirements

For this design example, use the parameters listed in [Table 2](#) as the input parameters.

Table 2. Design Parameters

DESIGN PARAMETER	REFERENCE	EXAMPLE VALUE
System bandwidth	f_{BW}	15 kHz

9.2.1.2 Detailed Design Procedure

The DRV5053 has internal filtering that limits the bandwidth to at least 20 kHz. For this application no external components are required other than the C1 bypass capacitor, which is 0.01 μ F minimum. If the analog output OUT is tied to a microcontroller ADC input, the equivalent load must be $R > 10$ k Ω and $C < 10$ nF.

Table 3. External Components

COMPONENT	PIN 1	PIN 2	RECOMMENDED
C1	V _{CC}	GND	A 0.01- μ F (minimum) ceramic capacitor rated for V _{CC}

9.2.1.3 Application Curve

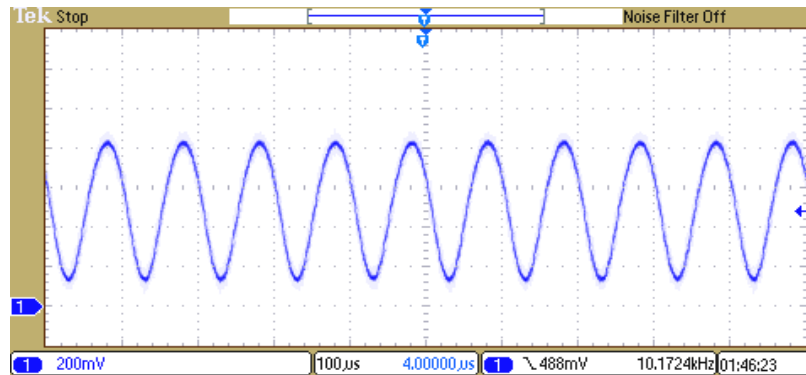


Figure 13. 10-kHz Switching Magnetic Field

9.2.2 Filtered Typical Application

For lower noise on the analog output OUT, additional RC filtering can be added to further reduce the bandwidth.

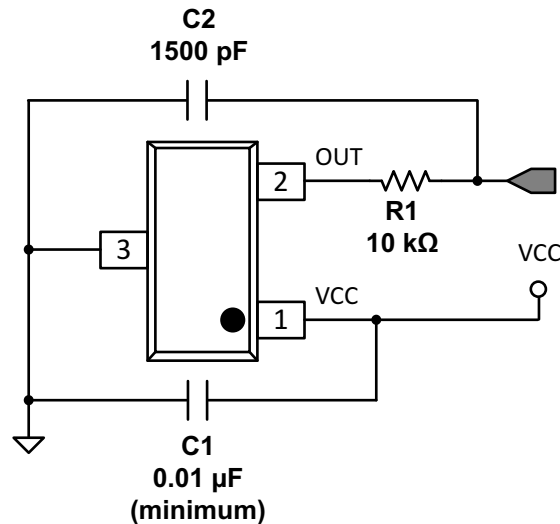


Figure 14. Filtered Typical Application Schematic

9.2.2.1 Design Requirements

For this design example, use the parameters listed in [Table 4](#) as the input parameters.

Table 4. Design Parameters

DESIGN PARAMETER	REFERENCE	EXAMPLE VALUE
System bandwidth	f_{BW}	5 kHz

9.2.2.2 Detailed Design Procedure

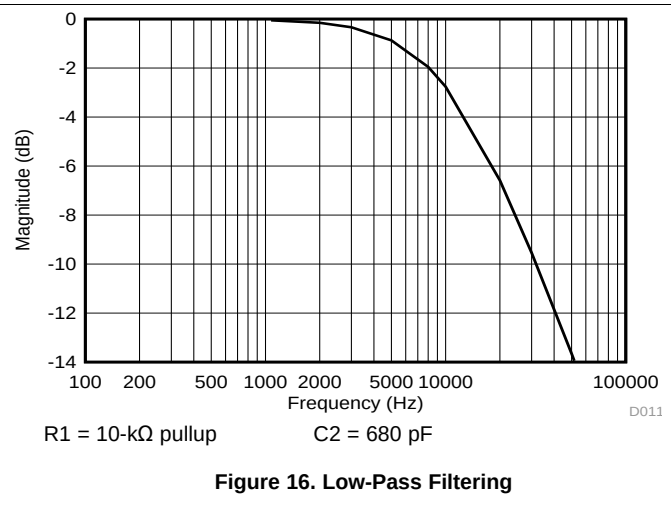
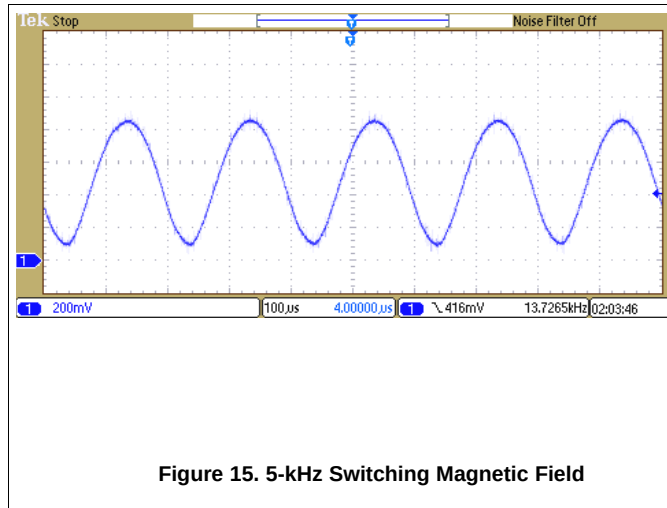
In this example we will add an external RC filter in order to reduce the output bandwidth.

In order to preserve the signal at the frequencies of interest, we will conservatively select a low-pass filter bandwidth (–3-dB point) at twice the system bandwidth (10 kHz).

$$10 \text{ kHz} < \frac{1}{2\pi \times R_1 \times C_2} \quad (1)$$

If we guess $R_1 = 10 \text{ k}\Omega$, then $C_2 < 1590 \text{ pF}$. So we select $C_2 = 1500 \text{ pF}$.

9.2.2.3 Application Curves



10 Power Supply Recommendations

The DRV5053 device is designed to operate from an input voltage supply (VM) range between 2.5 and 38 V. A 0.01-μF (minimum) ceramic capacitor rated for V_{CC} must be placed as close to the DRV5053 device as possible.

11 器件和文档支持

11.1 器件支持

11.1.1 器件命名规则

图 17 显示了读取 DRV5053 器件完整器件名称的图例。

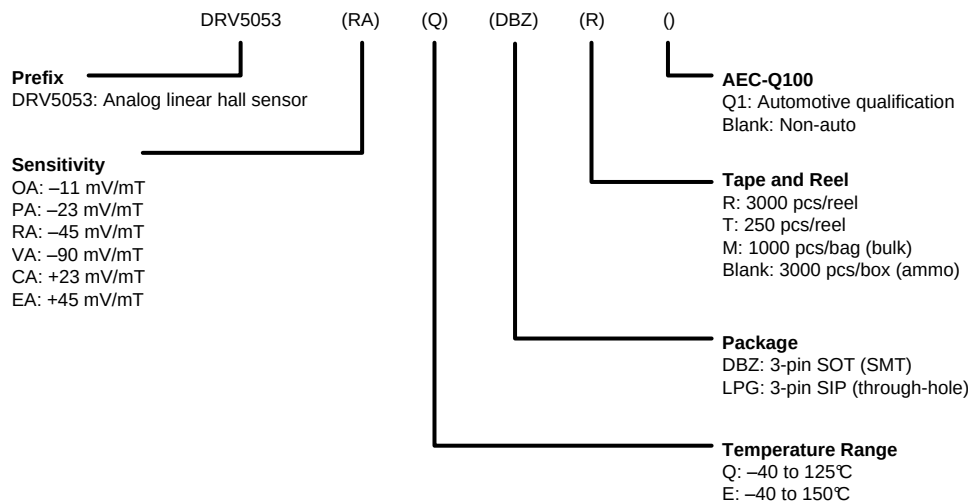


图 17. 器件命名规则

11.1.2 器件标记

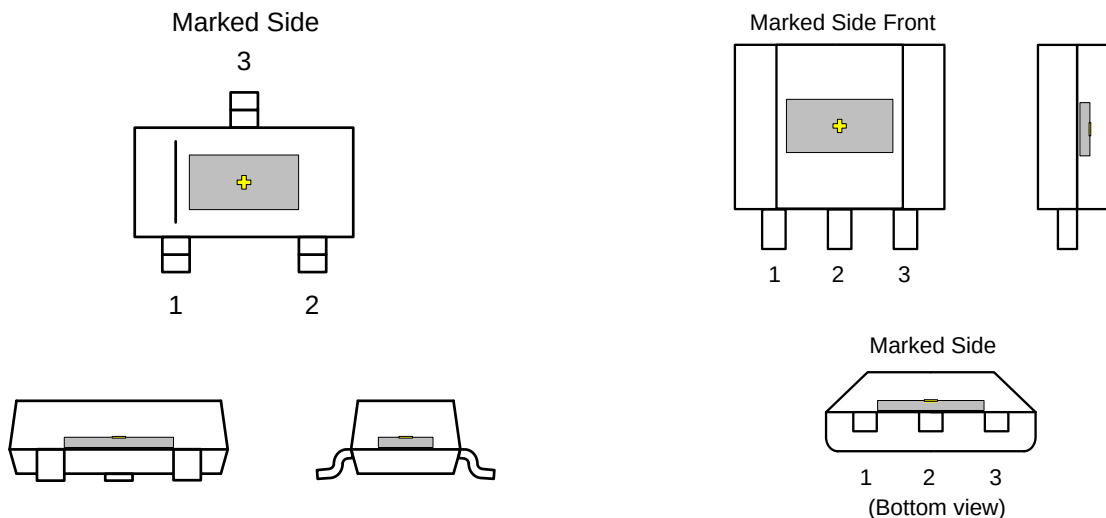


图 18. SOT-23 (DBZ) 封装

图 19. SIP (LPG) 封装

✚ 表示霍尔效应传感器（未按比例显示）。霍尔元件置于封装中央位置，容差为 $\pm 100\mu\text{m}$ 。在 DBZ 封装中，霍尔元件与封装底部的距离为 $0.7\text{mm} \pm 50\mu\text{m}$ ；在 LPG 封装中，霍尔元件与封装底部的距离为 $0.987\text{mm} \pm 50\mu\text{m}$ 。

11.2 商标

All trademarks are the property of their respective owners.

11.3 静电放电警告



这些装置包含有限的内置 ESD 保护。存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

11.4 术语表

[SLYZ022](#) — TI 术语表。

这份术语表列出并解释术语、首字母缩略词和定义。

12 机械封装和可订购信息

以下页中包括机械封装和可订购信息。 这些信息是针对指定器件可提供的最新数据。 这些数据会在无通知且不对本文档进行修订的情况下发生改变。 欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

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在某些场合中, 为了推进安全相关应用有可能对 TI 组件进行特别的促销。TI 的目标是利用此类组件帮助客户设计和创立其特 有的可满足适用的功能安全性标准和要求的终端产品解决方案。尽管如此, 此类组件仍然服从这些条款。

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	产品		应用
数字音频	www.ti.com.cn/audio	通信与电信	www.ti.com.cn/telecom
放大器和线性器件	www.ti.com.cn/amplifiers	计算机及周边	www.ti.com.cn/computer
数据转换器	www.ti.com.cn/dataconverters	消费电子	www.ti.com.cn/consumer-apps
DLP® 产品	www.dlp.com	能源	www.ti.com.cn/energy
DSP - 数字信号处理器	www.ti.com.cn/dsp	工业应用	www.ti.com.cn/industrial
时钟和计时器	www.ti.com.cn/clockandtimers	医疗电子	www.ti.com.cn/medical
接口	www.ti.com.cn/interface	安防应用	www.ti.com.cn/security
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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
DRV5053CAQDBZR	ACTIVE	SOT-23	DBZ	3	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	+ALCA	Samples
DRV5053CAQDBZT	ACTIVE	SOT-23	DBZ	3	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	+ALCA	Samples
DRV5053CAQLPG	ACTIVE	TO-92	LPG	3	1000	Green (RoHS & no Sb/Br)	CU SN	N / A for Pkg Type	-40 to 125	+ALCA	Samples
DRV5053CAQLPGM	ACTIVE	TO-92	LPG	3	3000	Green (RoHS & no Sb/Br)	CU SN	N / A for Pkg Type	-40 to 125	+ALCA	Samples
DRV5053EAQDBZR	ACTIVE	SOT-23	DBZ	3	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	+ALEA	Samples
DRV5053EAQDBZT	ACTIVE	SOT-23	DBZ	3	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	+ALEA	Samples
DRV5053EAQLPG	ACTIVE	TO-92	LPG	3	1000	Green (RoHS & no Sb/Br)	CU SN	N / A for Pkg Type	-40 to 125	+ALEA	Samples
DRV5053EAQLPGM	ACTIVE	TO-92	LPG	3	3000	Green (RoHS & no Sb/Br)	CU SN	N / A for Pkg Type	-40 to 125	+ALEA	Samples
DRV5053OAQDBZR	ACTIVE	SOT-23	DBZ	3	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	+ALOA	Samples
DRV5053OAQDBZT	ACTIVE	SOT-23	DBZ	3	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	+ALOA	Samples
DRV5053OAQLPG	ACTIVE	TO-92	LPG	3	1000	Green (RoHS & no Sb/Br)	CU SN	N / A for Pkg Type	-40 to 125	+ALOA	Samples
DRV5053OAQLPGM	ACTIVE	TO-92	LPG	3	3000	Green (RoHS & no Sb/Br)	CU SN	N / A for Pkg Type	-40 to 125	+ALOA	Samples
DRV5053PAQDBZR	ACTIVE	SOT-23	DBZ	3	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	+ALPA	Samples
DRV5053PAQDBZT	ACTIVE	SOT-23	DBZ	3	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	+ALPA	Samples
DRV5053PAQLPG	ACTIVE	TO-92	LPG	3	1000	Green (RoHS & no Sb/Br)	CU SN	N / A for Pkg Type	-40 to 125	+ALPA	Samples
DRV5053PAQLPGM	ACTIVE	TO-92	LPG	3	3000	Green (RoHS & no Sb/Br)	CU SN	N / A for Pkg Type	-40 to 125	+ALPA	Samples
DRV5053RAQDBZR	ACTIVE	SOT-23	DBZ	3	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	+ALRA	Samples

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
DRV5053RAQDBZT	ACTIVE	SOT-23	DBZ	3	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	+ALRA	Samples
DRV5053RAQLPG	ACTIVE	TO-92	LPG	3	1000	Green (RoHS & no Sb/Br)	CU SN	N / A for Pkg Type	-40 to 125	+ALRA	Samples
DRV5053RAQLPGM	ACTIVE	TO-92	LPG	3	3000	Green (RoHS & no Sb/Br)	CU SN	N / A for Pkg Type	-40 to 125	+ALRA	Samples
DRV5053VAQDBZR	ACTIVE	SOT-23	DBZ	3	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	+ALVA	Samples
DRV5053VAQDBZT	ACTIVE	SOT-23	DBZ	3	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	+ALVA	Samples
DRV5053VAQLPG	ACTIVE	TO-92	LPG	3	1000	Green (RoHS & no Sb/Br)	CU SN	N / A for Pkg Type	-40 to 125	+ALVA	Samples
DRV5053VAQLPGM	ACTIVE	TO-92	LPG	3	3000	Green (RoHS & no Sb/Br)	CU SN	N / A for Pkg Type	-40 to 125	+ALVA	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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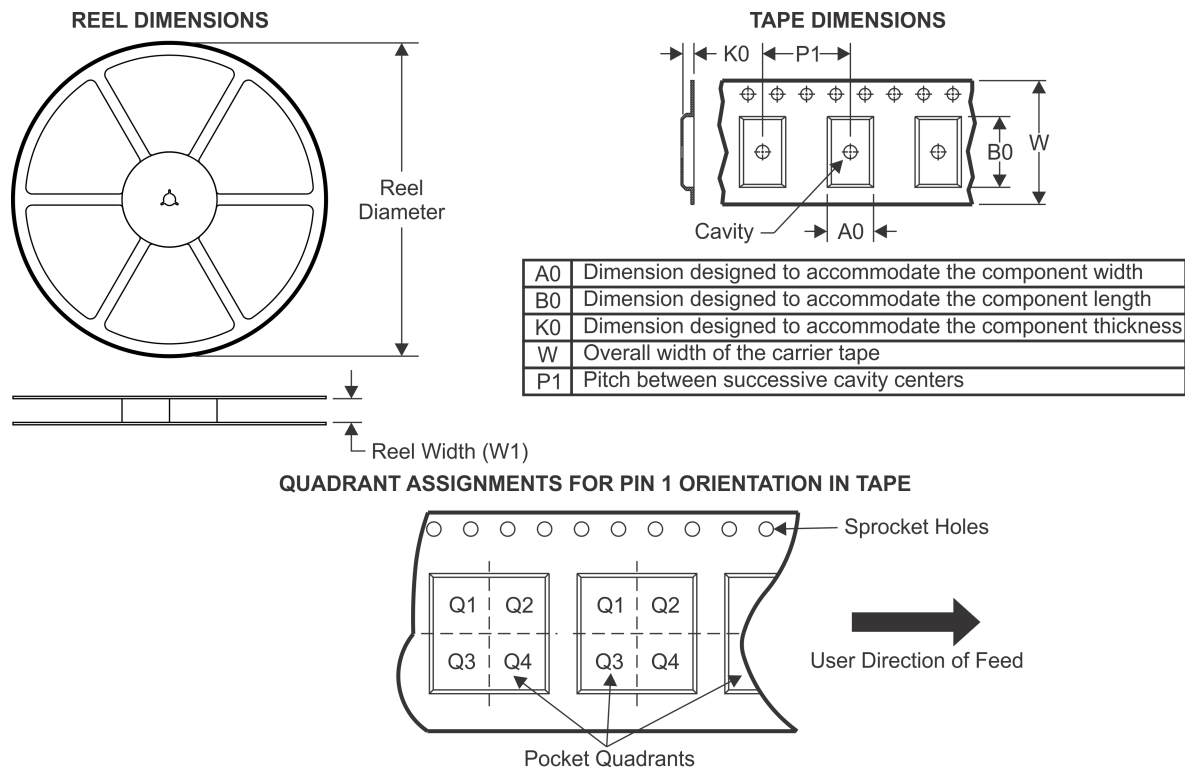
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF DRV5053 :

- Automotive: [DRV5053-Q1](#)

NOTE: Qualified Version Definitions:

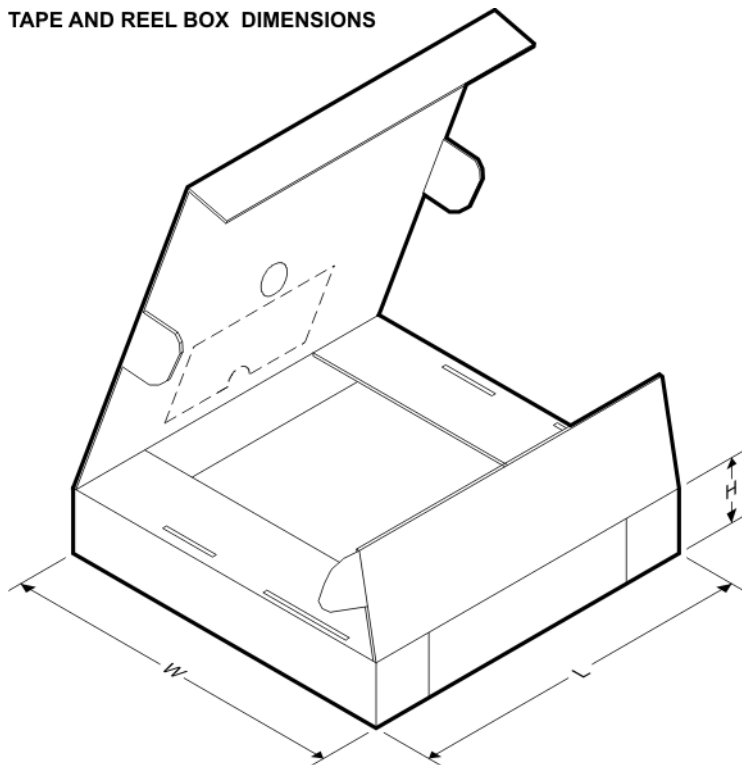
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION


*All dimensions are nominal

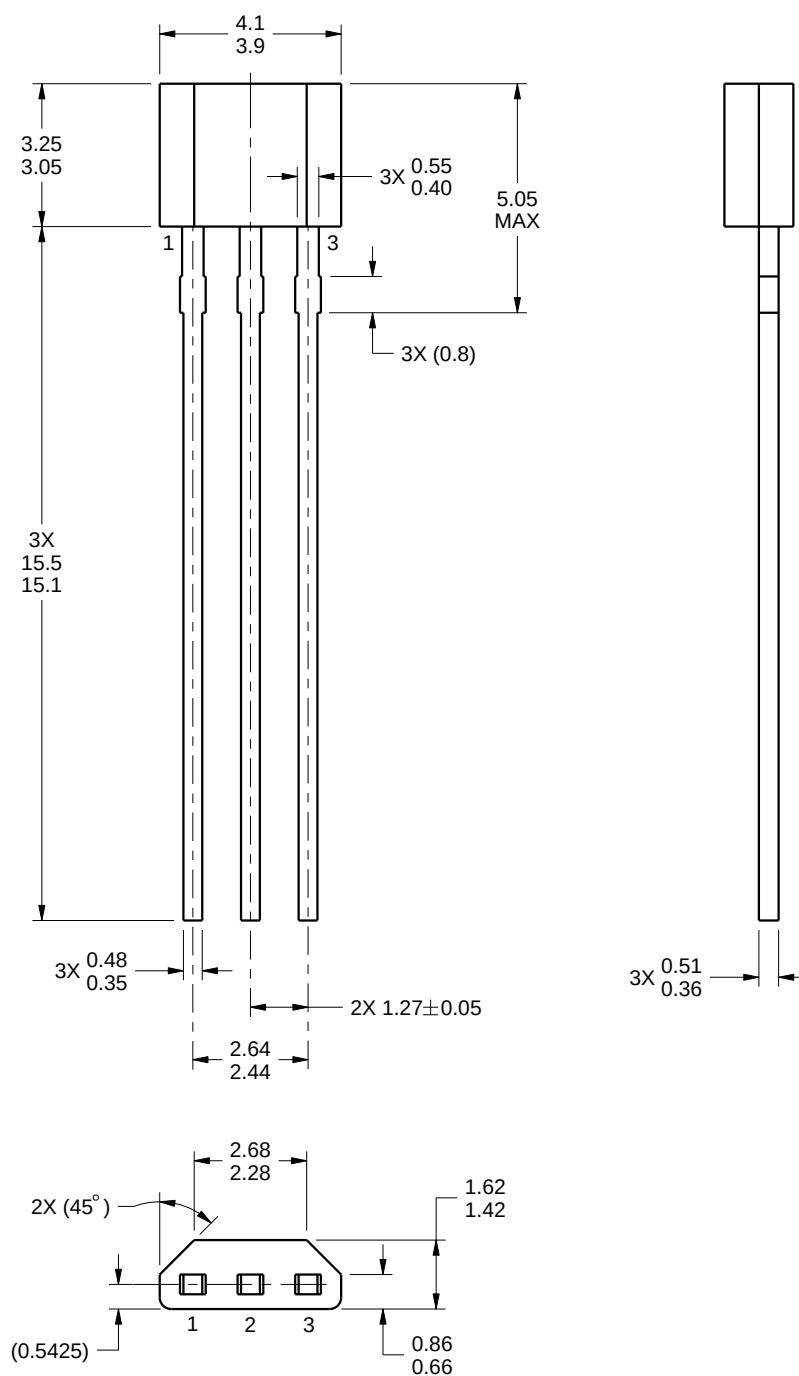
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
DRV5053CAQDBZR	SOT-23	DBZ	3	3000	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3
DRV5053CAQDBZT	SOT-23	DBZ	3	250	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3
DRV5053EAQDBZR	SOT-23	DBZ	3	3000	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3
DRV5053EAQDBZT	SOT-23	DBZ	3	250	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3
DRV5053OAQDBZR	SOT-23	DBZ	3	3000	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3
DRV5053OAQDBZT	SOT-23	DBZ	3	250	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3
DRV5053PAQDBZR	SOT-23	DBZ	3	3000	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3
DRV5053PAQDBZT	SOT-23	DBZ	3	250	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3
DRV5053RAQDBZR	SOT-23	DBZ	3	3000	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3
DRV5053RAQDBZT	SOT-23	DBZ	3	250	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3
DRV5053VAQDBZR	SOT-23	DBZ	3	3000	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3
DRV5053VAQDBZT	SOT-23	DBZ	3	250	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
DRV5053CAQDBZR	SOT-23	DBZ	3	3000	202.0	201.0	28.0
DRV5053CAQDBZT	SOT-23	DBZ	3	250	202.0	201.0	28.0
DRV5053EAQDBZR	SOT-23	DBZ	3	3000	202.0	201.0	28.0
DRV5053EAQDBZT	SOT-23	DBZ	3	250	202.0	201.0	28.0
DRV5053OAQDBZR	SOT-23	DBZ	3	3000	202.0	201.0	28.0
DRV5053OAQDBZT	SOT-23	DBZ	3	250	202.0	201.0	28.0
DRV5053PAQDBZR	SOT-23	DBZ	3	3000	202.0	201.0	28.0
DRV5053PAQDBZT	SOT-23	DBZ	3	250	202.0	201.0	28.0
DRV5053RAQDBZR	SOT-23	DBZ	3	3000	202.0	201.0	28.0
DRV5053RAQDBZT	SOT-23	DBZ	3	250	202.0	201.0	28.0
DRV5053VAQDBZR	SOT-23	DBZ	3	3000	202.0	201.0	28.0
DRV5053VAQDBZT	SOT-23	DBZ	3	250	202.0	201.0	28.0



4221343/B 09/2016

NOTES:

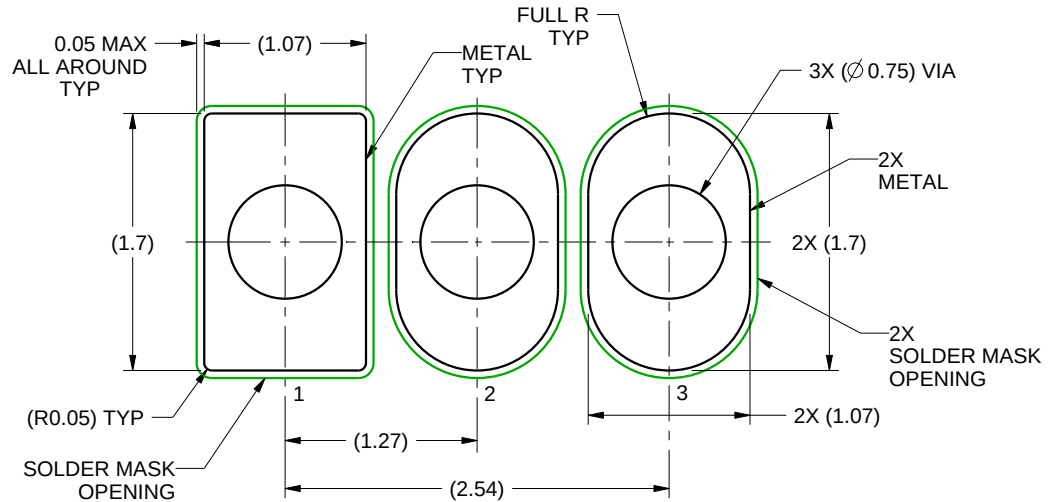
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

EXAMPLE BOARD LAYOUT

LPG0003A

TO-92 - 5.05 mm max height

TO-92



LAND PATTERN EXAMPLE
NON-SOLDER MASK DEFINED
SCALE:20X

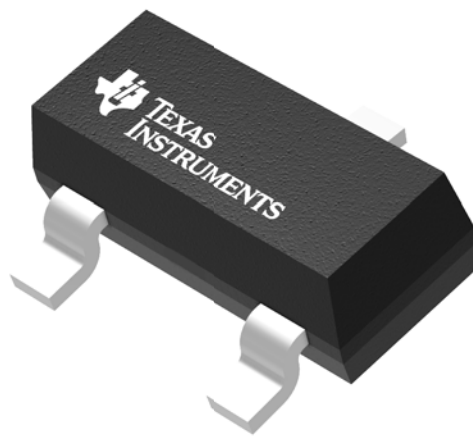
4221343/B 09/2016

GENERIC PACKAGE VIEW

DBZ 3

SOT-23 - 1.12 mm max height

SMALL OUTLINE TRANSISTOR



Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

4203227/C

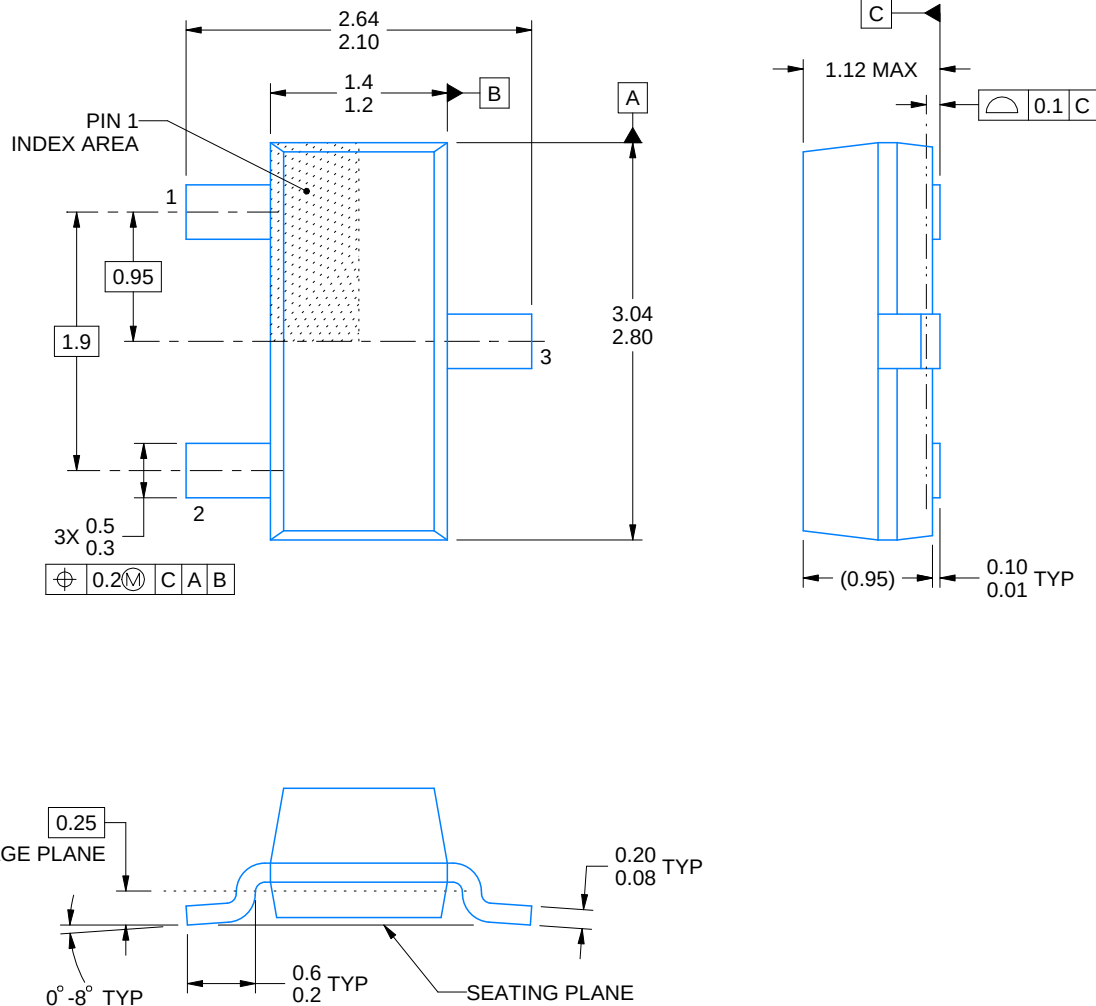
DBZ0003A



PACKAGE OUTLINE

SOT-23 - 1.12 mm max height

SMALL OUTLINE TRANSISTOR



4214838/C 04/2017

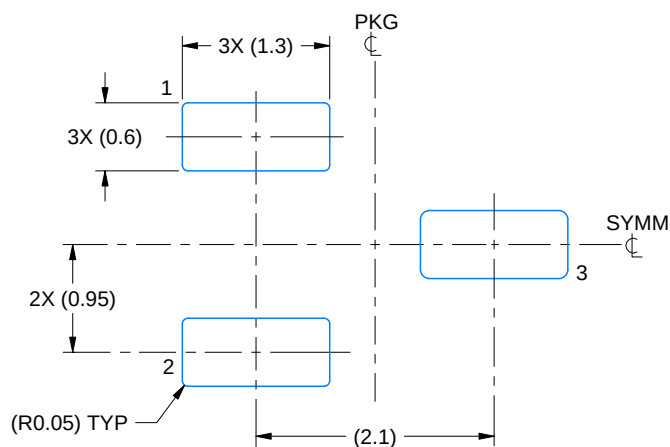
NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC registration TO-236, except minimum foot length.

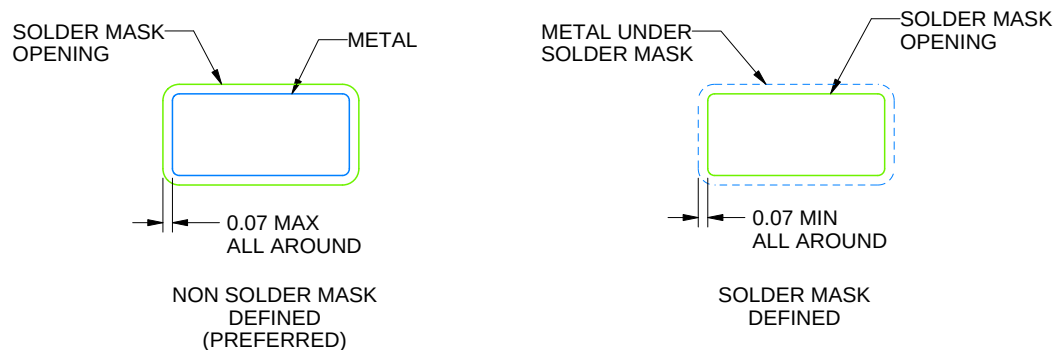
DBZ0003A

SOT-23 - 1.12 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
SCALE:15X



SOLDER MASK DETAILS

4214838/C 04/2017

NOTES: (continued)

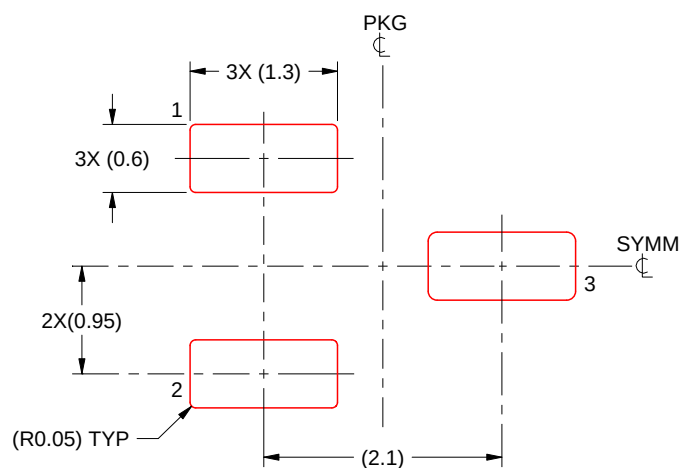
4. Publication IPC-7351 may have alternate designs.
5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBZ0003A

SOT-23 - 1.12 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE:15X

4214838/C 04/2017

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
7. Board assembly site may have different recommendations for stencil design.

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